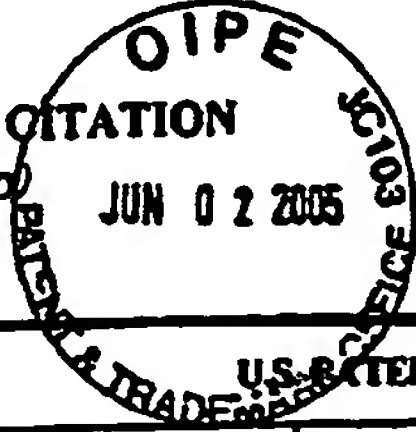


INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)				Docket Number (Optional) BUR920040040US1		Application Number 10/71170	
				Applicant(s) Anderson, et al.			



U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
HQA		6660596	2003-12-09	Adkisson, et al	438	286	—
HQA		6635923	2003-10-21	Honafi, et al	257	327	—
HQA		6118161	2000-04-12	Chapman, et al	257	401	—

U.S. PATENT APPLICATION PUBLICATIONS							
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
HQA		20030178670	2003-09-25	Fried, et al	257	315	—
HQA		20030151077	2003-08-14	Mattewi, et al	257	250	—

FOREIGN PATENT DOCUMENTS							
REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS			(Including Author, Title, Date, Pertinent Pages, Etc.)
HQA		Lindert, et al, "Sub-60-nm Quasi-Planar FinFETs Fabricated Using a Simplified Process", IEEE Electron Device Letters, Vol 22, No. 10, October 2001, Pages 487-489	

EXAMINER HOANG-QUAN HO	DATE CONSIDERED 9/15/05
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.